# **TDA8559T**

# Low-voltage stereo headphone amplifier

Rev. 03 — 15 May 2006

**Product data sheets** 

# 1. General description

The TDA8559T is a stereo amplifier that operates over a wide supply voltage range from 1.9 V to 30 V and consumes a very low quiescent current. This makes it suitable for battery fed applications ( $2 \times 1.5$  V cells). Because of an internal voltage buffer, this device can be used with or without a capacitor connected in series with the load. It can be applied as a headphone amplifier, but also as a mono amplifier with a small speaker ( $25 \Omega$ ), or as a line driver in mains applications.

#### 2. Features

- Operating voltage from 1.9 V to 30 V
- Very low quiescent current
- Low distortion
- Few external components
- Differential inputs
- Usable as a mono amplifier in Bridge-Tied Load (BTL) or stereo Single-Ended (SE)
- Single-ended mode without loudspeaker capacitor
- Mute and Standby mode
- Short-circuit proof to ground, to supply voltage (< 10 V) and across load
- No switch on or switch off clicks
- ESD protected on all pins

# 3. Applications

- Portable telephones
- MP3 players
- Portable audio
- Mains fed equipment



## Low-voltage stereo headphone amplifier

# 4. Quick reference data

Table 1. Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Supplies						
$V_{P}$	operating supply voltage		1.9	3	30	V
$I_{q(tot)}$	total quiescent current	open load	-	2.75	4	mA
I <sub>stb</sub>	standby supply current	open load	-	-	10	μΑ
Stereo ap	plication					
Po	output power	THD = 10 %	30	35	-	mW
THD	total harmonic distortion	$P_o = 20 \text{ mW};$ $f_i = 1 \text{ kHz}$	<u>[1]</u> -	0.075	0.15	%
		$P_o = 20 \text{ mW};$ $f_i = 10 \text{ kHz}$	<u>[1]</u> -	0.1	-	%
$G_v$	voltage gain		25	26	27	dB
f <sub>ss</sub>	small signal roll-off frequency	–1 dB	-	750	-	kHz
BTL appli	ication					
Po	output power	THD = 10 %	125	140	-	mW
THD	total harmonic distortion	$P_o = 70 \text{ mW};$ $f_i = 1 \text{ kHz}$	-	0.05	0.1	%
		$P_o = 70 \text{ mW};$ $f_i = 10 \text{ kHz}$	-	0.1	-	%
$G_v$	voltage gain		31	32	33	dB

<sup>[1]</sup> Measured with low-pass filter 30 kHz.

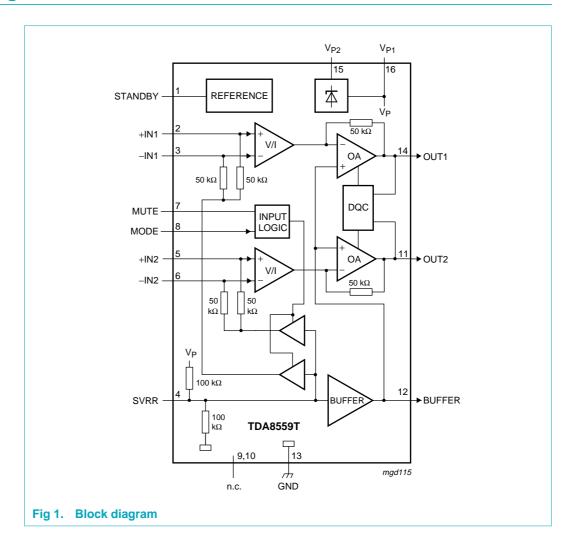
# 5. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
TDA8559T	SO16	plastic small outline package; 16 leads; body width 3.9 mm; body thickness 1.47 mm	SOT109-1

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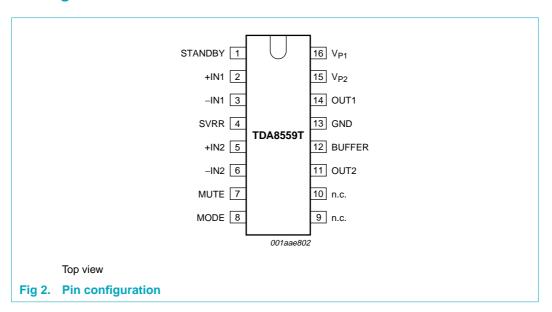
# 6. Block diagram



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# 7. Pinning information

# 7.1 Pinning



# 7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
STANDBY	1	standby select
+IN1	2	non-inverting input 1
-IN1	3	inverting input 1
SVRR	4	supply voltage ripple rejection
+IN2	5	non-inverting input 2
-IN2	6	inverting input 2
MUTE	7	mute select
MODE	8	input mode select
n.c.	9	not connected
n.c.	10	not connected
OUT2	11	output 2
BUFFER	12	buffer output (0.5V <sub>P</sub> )
GND	13	ground
OUT1	14	output 1
$V_{P2}$	15	high supply voltage
$V_{P1}$	16	low supply voltage

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# 8. Functional description

The TDA8559T contains two amplifiers with differential inputs, a  $0.5V_P$  output buffer and a high supply voltage stabilizer. Each amplifier consists of a voltage-to-current converter (V/I), an output amplifier and a common dynamic quiescent current controller. The gain of each amplifier is internally fixed at 26 dB (=  $20 \times$ ). The  $0.5V_P$  output can be used as a replacement for the single-ended capacitors. The two amplifiers can also be used as a mono amplifier in a BTL configuration thereby resulting in more output power.

With three mode select pins, the device can be switched into the following modes:

- 1. Standby mode ( $I_P < 10 \mu A$ )
- 2. Mute mode
- 3. Operation mode, with two input selections (the input source is directly connected or connected via coupling capacitors at the input).

The ripple rejection in the stereo application with a single-ended capacitor can be improved by connecting a capacitor between the 0.5V<sub>P</sub> capacitor pin and ground.

The device is fully protected against short-circuiting of the output pins to ground, to the low supply voltage pin and across the load.

#### 8.1 V/I converters

The V/I converters have a transconductance of  $400~\mu S$ . The inputs are completely symmetrical and the two amplifiers can be used in opposite phase. The Mute mode causes the V/I converters to block the input signal. The input mode pin selects two applications in which the V/I converters can be used.

The first application (input mode pin floating) is used with a supply voltage below 6 V. The input DC level is at ground level (the unused input pin connected to ground) and no input coupling capacitors are necessary. The maximum converter output current is sufficient to obtain an output swing of 3 V (peak).

In the second application with a supply voltage greater than 6 V (input mode pin HIGH), the input mode pin is connected to  $V_P$ . In this configuration (input DC level is  $0.5V_P + 0.6$  V) the input source must be coupled with a capacitor and the two unused input pins must be connected via a capacitor to ground, to improve noise performance. This application has a higher quiescent current, because the maximum output current of the V/I converter is higher to obtain an output voltage swing of 9 V (peak).

#### 8.2 Output amplifiers

The output amplifiers have a transresistance of 50 k $\Omega$ , a bandwidth of approximately 750 kHz and a maximum output current of 100 mA. The mid-tap output voltage equals the voltage applied at the non-inverting pin of the output amplifier. This pin is connected to the output of the 0.5V $_{\rm P}$  buffer. This reduces the distortion when the load is connected between an output amplifier and the buffer (because feedback is applied over the load).

#### 8.3 Buffer

The buffer delivers  $0.5V_P$  to the output with a maximum output (sink and source) current of 200 mA (peak).

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### 8.4 Dynamic quiescent controller

The Dynamic Quiescent Current controller (DQC) gives the advantage of low quiescent current and low distortion. When there are high frequencies in the output signal, the DQC will increase the quiescent current of the two output amplifiers and the buffer. This will reduce the crossover distortion that normally occurs at high frequencies and low quiescent current. The DQC gives output currents that are linear with the amplitude and the frequency of the output signals. These currents control the quiescent current.

#### 8.5 Stabilizer

The TDA8559T has a voltage supply range from 1.9 V to 30 V. This range is divided over two supply voltage pins. Pin 16 is 1.9 V to 18 V (breakdown voltage of the process); this pin is preferred for supply voltages less than 18 V. Pin 15 is used for applications where  $V_P$  is approximately 6 V to 30 V. The stabilizer output is internally connected to the supply voltage pin 16. In the range from 6 V to 18 V, the voltage drop to pin 16 is 1 V. In the range from 18 V to 30 V the stabilizer output voltage (to pin 16) is approximately 17 V.

#### 8.6 Input logic

The MUTE pin (pin 7) selects the Mute mode of the V/I converters. LOW (TTL/CMOS) level is mute. A voltage between 0.5 V (low level) and 1.5 V (high level) causes a soft mute to operate (no plops). When pin 7 is floating or greater than 1.5 V it is in the operating condition.

The input mode pin must be connected to  $V_P$  when the supply voltage is greater than 6 V. The input mode logic raises the tail current of the V/I converters and enables the two buffers to bias the inputs of the V/I converters.

#### 8.7 Reference

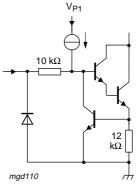
This circuit supplies all currents needed in this device. With the Standby mode pin 1 (TTL/CMOS), it is possible to switch to the Standby mode and reduce the total quiescent current to below 10  $\mu$ A.

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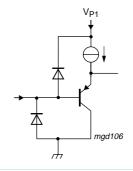
# 9. Internal circuitry

Table 4. Internal circuits

Symbol	Pin	Equivalent circuit
STANDBY	1	



+IN1, -IN1, +IN2  $\,$  2, 3, 5 and 6 and -IN2



SVRR 4

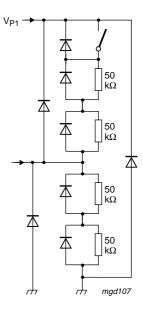
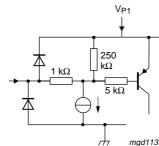


 Table 4.
 Internal circuits ...continued

Symbol	Pin	Equivalent circuit
MUTE	7	VP1
MODE	8	



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 Table 4.
 Internal circuits ...continued

**Symbol** Pin **Equivalent circuit** OUT2 and OUT1 11 and 14 100  $\Omega$ buffer output mgd108 BUFFER 12 本 - buffer output 本 mgd109  $V_{P2}$  and  $V_{P1}$ 15 and 16  $V_{P1}$ 2 kΩ 本 mgd111

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# 10. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{P2(max)}$	maximum supply voltage (pin 15)		-	30	V
$V_{P1(max)}$	maximum supply voltage (pin 16)		-	18	V
$V_{i(max)}$	maximum input voltage		-	18	V
I <sub>ORM</sub>	peak output current	repetitive	-	150	mA
P <sub>tot</sub>	total power dissipation		-	1.19	W
T <sub>amb</sub>	ambient temperature		-40	+85	°C
T <sub>stg</sub>	storage temperature		<b>–55</b>	+150	°C
$T_{vj}$	virtual junction temperature		-	150	°C
t <sub>sc</sub>	short-circuiting time	$V_P < 10 \text{ V}$	-	1	h

## 11. Thermal characteristics

#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	105	K/W

# 12. Characteristics

Table 7. Characteristics

 $V_P = 3 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ ;  $f_i = 1 \text{ kHz}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
DC charac	teristics					
V <sub>P</sub>	operating supply voltage		<u>[1]</u> 1.9	3	30	V
I <sub>q(tot)</sub>	total quiescent current	open load	-	2.75	4	mA
I <sub>stb</sub>	standby supply current	open load	-	-	10	μΑ
V <sub>1</sub>	Standby mode voltage	standby	0	-	0.5	V
		operating	1.5	-	18	V
V <sub>7</sub>	Mute mode voltage	mute	0	-	0.5	V
		operating	1.5	-	18	V
I <sub>bias</sub>	input bias current		-	100	300	nA
Single-end	led stereo application ( $R_L$ =	<b>32</b> Ω)				
Po	output power	THD = 10 %	30	35	-	mW
THD	total harmonic distortion	$P_0 = 20 \text{ mW}; f_i = 1 \text{ kHz}$	[2] -	0.075	0.15	%
		$P_0 = 20 \text{ mW}; f_i = 10 \text{ kHz}$	[2] -	0.1	-	%
G <sub>v</sub>	voltage gain		25	26	27	dB
f <sub>ss</sub>	small signal roll-off frequency	–1 dB	-	750	-	kHz
$\alpha_{ t CS}$	channel separation	$R_s = 5 \text{ k}\Omega$	40	-	-	dB
$ \Delta G_v $	channel unbalance		-	-	1	dB

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Table 7. Characteristics ... continued

 $V_P = 3 \text{ V; } T_{amb} = 25 \,^{\circ}\text{C; } f_i = 1 \text{ kHz; unless otherwise specified.}$ 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{no}$	noise output voltage		[3]	-	70	85	μV
V <sub>no(mute)</sub>	noise output voltage in mute		[3]	-	20	30	μV
$V_{o(mute)}$	output voltage in mute		<u>[4]</u>	-	-	30	μV
$V_{mt}$	mid-tap voltage			1.4	1.5	1.6	V
Zi	input impedance			75	100	125	$k\Omega$
Vos	DC output offset voltage		<u>[5]</u>	-	-	100	mV
SVRR	supply voltage ripple rejection		[6]	45	55	-	dB
BTL applic	eation ( $R_L = 25 \Omega$ )						
Po	output power	THD = 10 %		125	140	-	mW
THD	total harmonic distortion	$P_o = 70 \text{ mW}$ ; $f_i = 1 \text{ kHz}$		-	0.05	0.1	%
		$P_0 = 70 \text{ mW}; f_i = 10 \text{ kHz}$		-	0.1	-	%
$G_{v}$	voltage gain			31	32	33	dB
$f_{ss}$	small signal roll-off frequency	–1 dB		-	750	-	kHz
$V_{no}$	noise output voltage		[3]	-	100	120	μV
V <sub>no(mute)</sub>	noise output voltage in mute		[3]	-	25	40	μV
V <sub>o(mute)</sub>	output voltage in mute		<u>[4]</u>	-	-	40	μV
Zi	input impedance			39	50	61	kΩ
Vos	DC output offset voltage		<u>[7]</u>	-	-	150	mV
SVRR	supply voltage ripple rejection		[6]	39	49	-	dB
Line drive	application ( $R_L = 1 \text{ k}\Omega$ )						
Vo	line output voltage			0.1	-	2.9	V

<sup>[1]</sup> The supply voltage range at pin  $V_{P1}$  is from 1.9 V to 18 V. Pin  $V_{P2}$  is used for the voltage range from 6 V to 30 V.

# 13. Application information

#### 13.1 General

For applications with a maximum supply voltage of 6 V (input mode low) the input pins need a DC path to ground (see <u>Figure 3</u> and <u>Figure 4</u>). For applications with supply voltages in the range from 6 V to 18 V (input mode HIGH) the input DC level is  $0.5V_P + 0.6$  V. In this situation the input configurations illustrated in <u>Figure 5</u> and <u>Figure 6</u> have to be used.

<sup>[2]</sup> Measured with low-pass filter 30 kHz.

<sup>[3]</sup> Noise output voltage measured with a bandwidth of 20 Hz to 20 kHz, unweighted.  $R_s = 5 \text{ k}\Omega$ .

<sup>[4]</sup> RMS output voltage in mute is measured with  $V_i$  = 200 mV (RMS); f = 1 kHz.

<sup>[5]</sup> DC output offset voltage is measured between the signal output and the 0.5V<sub>P</sub> output.

<sup>[6]</sup> The ripple rejection is measured with a ripple voltage of 200 mV (RMS) applied to the positive supply rail ( $R_s = 0 \text{ k}\Omega$ ).

<sup>[7]</sup> DC output offset voltage is measured between the two signal outputs.

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The capacitor Cb is recommended for stability improvement. The value may vary between 10 nF and 100 nF. This capacitor should be placed close to the IC between pin 12 and pin 13.

#### 13.2 Heatsink design

The standard application is stereo headphone single-ended with a 32  $\Omega$  load impedance to buffer (see Figure 9). The headphone amplifier can deliver a peak output current of 150 mA into the load.

For the SO16 envelope  $R_{th(j-a)} = 105$  K/W; the maximum sinewave power dissipation for  $T_{amb} = 25$  °C is: 1.2 W =  $\frac{150-25}{105}$ 

For  $T_{amb} = 60$  °C the maximum total power dissipation is:  $0.85 \text{ W} = \frac{150 - 60}{105}$ 

#### 13.3 Test conditions

 $T_{amb}$  = 25 °C; unless otherwise specified:  $V_P$  = 3 V, f = 1 kHz,  $R_L$  = 32  $\Omega$ , Gain = 26 dB, low input mode, band-pass filter: 22 Hz to 30 kHz. The total harmonic distortion as a function of frequency was measured with low-pass filter of 80 kHz. The quiescent current has been measured without any load impedance.

In applications with coupling capacitors towards the load, an electrolytic capacitor has to be connected to pin 4 (SVRR).

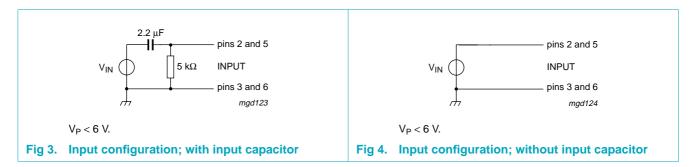
- 1. The graphs for the single-ended application have been measured with the application illustrated in <u>Figure 9</u>; input configuration for input mode low (<u>Figure 4</u>) and input configuration for input mode high (<u>Figure 6</u>).
- The graphs for the BTL application 'input mode low' have been measured with the application circuit illustrated in <u>Figure 11</u> and the input configuration illustrated in <u>Figure 4</u>.
- The graphs for the line-driver application have been measured with the application circuit illustrated in <u>Figure 13</u> and the input configuration illustrated in <u>Figure 6</u>; input mode high.

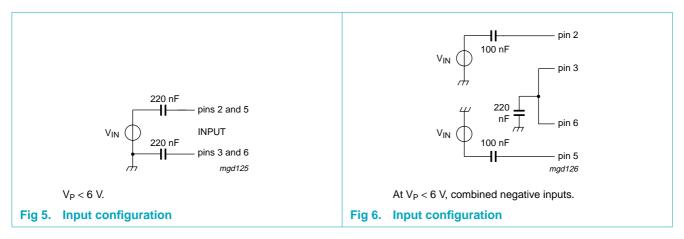
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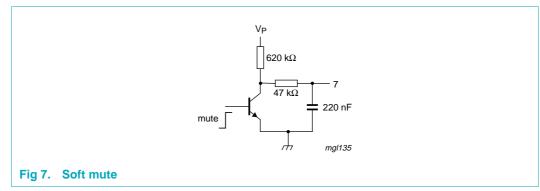
## 13.4 Input configurations

The IC can be applied in two ways, 'input mode low' and 'input mode high'. This can be selected by the input mode at pin 8:

- 1. Input mode low: pin 8 floating: The DC level of the input pins has to be between 0 V and ( $V_P 1.8 \text{ V}$ ). A DC path to ground is needed. The maximum output voltage is approximately 2.1 V (RMS). Input configurations illustrated in Figure 3 and Figure 4 should be used.
- 2. Input mode high: pin 8 is connected to  $V_P$ : This mode is intended for supply voltages > 6 V. It can deliver a maximum output voltage of approximately 6 V (RMS) at THD = 0.5 %. The DC voltage level of the input pins is  $(0.5V_P + 0.6 \text{ V})$ . Coupling capacitors are necessary. Input configurations illustrated in Figure 5 and Figure 6 should be used.







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### 13.5 Standby/mute

- 1. The Standby mode ( $V_1$  < 0.5 V) is intended for power saving purpose. Then the total quiescent current is < 10  $\mu$ A.
- 2. To avoid 'pop-noise' during switch-on or switch-off the IC can be muted ( $V_7 < 0.5 \text{ V}$ ). This can be achieved by a 'soft-mute' circuit or by direct control from a microcontroller.

#### 13.6 Application 1: SE with loudspeaker capacitor

The value of capacitor Cr influences the behavior of the Supply Voltage Ripple Rejection (SVRR) at low frequencies; increasing the value of Cr increases the performance of the SVRR; see Figure 8.

### 13.7 Application 2: SE to buffer (without loudspeaker capacitor)

This is the basic headphone application. The advantage of this application with respect to application 1, is that it needs only one external component (Cb) in the event of stability problems; see Figure 9.

# 13.8 Application 3: Improved SE to buffer (without loudspeaker capacitor)

This application is an improved configuration of application 2. The distinction between the two is connecting the loads in opposite phase. This lowers the average current through the SE buffer. It should be noted that a headphone cannot be used because the load requires floating terminals; see Figure 10.

### 13.9 Application 4: Bridge tied load mono amplifier

This configuration delivers four times the output power of the SE application with the same supply and load conditions. The capacitor Cr is not required; see Figure 11.

### 13.10 Application 5: Line driver application

The TDA8559T delivers a virtual rail-to-rail output voltage and is also usable in a low voltage environment, as a line driver. In this application the input needs a DC path to ground, input configurations illustrated in <a href="Figure 3">Figure 4</a> should be used. The value of capacitor Cr influences the behavior of the SVRR at low frequencies; increasing the value of Cr increases the performance of the SVRR; see <a href="Figure 12">Figure 12</a>.

#### 13.11 Application 6: Line driver application

The TDA8559T delivers a virtual rail-to-rail output voltage. Because the input mode has to be high, the input configurations illustrated in <u>Figure 5</u> and <u>Figure 6</u> should be used. This application can also be used for headphone application, however, due to the limited output current and the limited output power at the headphone, series resistors have to be used between the output pins and the load; see <u>Figure 13</u>.

The value of capacitor Cr influences the behavior of the SVRR at low frequencies; increasing the value of Cr increases the performance of the SVRR.

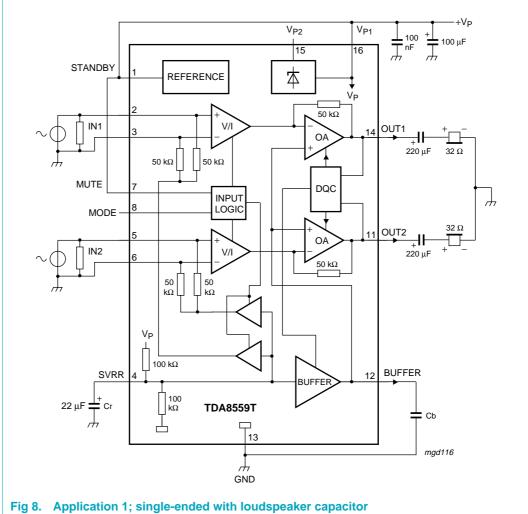
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### 13.12 Application 7: Line driver application

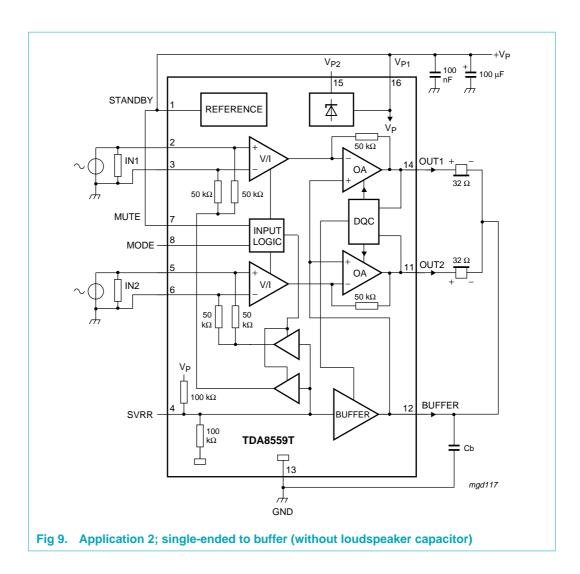
With the supply voltage connected to pin 15 it is possible to use the head amplifier above the maximum of 18 V to pin 16. The internal supply voltage will be reduced to a maximum of approximately 17 V.

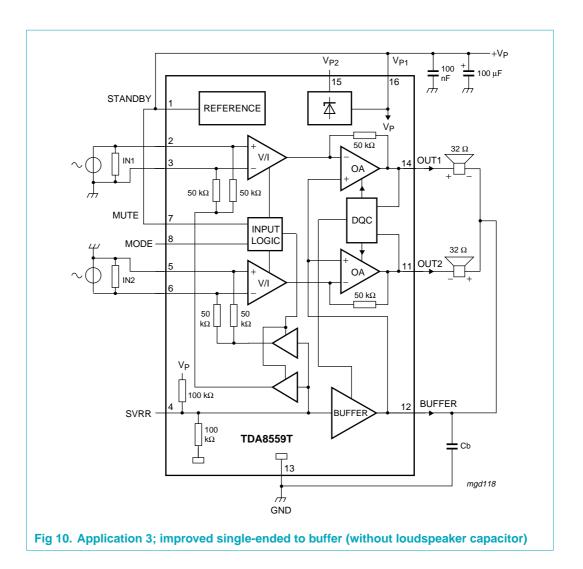
This will be convenient in applications where the supply voltage is higher than 18 V, however an output voltage swing that reaches the higher supply voltage is not required. the input configurations illustrated in <a href="Figure 5">Figure 5</a> and <a href="Figure 6">Figure 6</a> should be used. This application can also be used for headphone applications. However, due to the limited output current, series resistors have to be used between the output pins and the load; see <a href="Figure 14">Figure 14</a>.

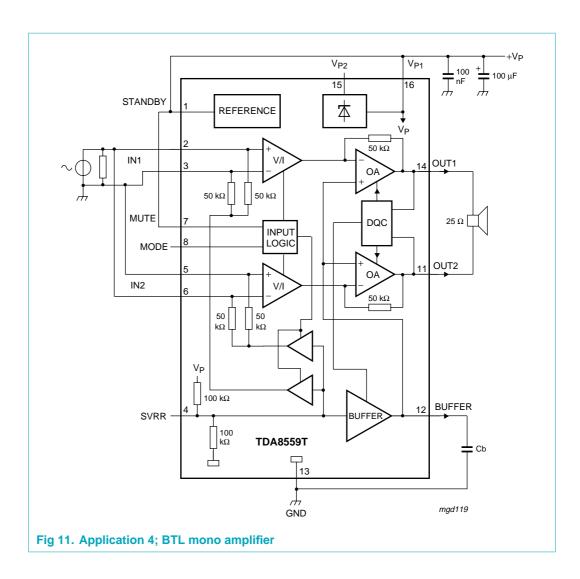
# 13.13 Application diagrams

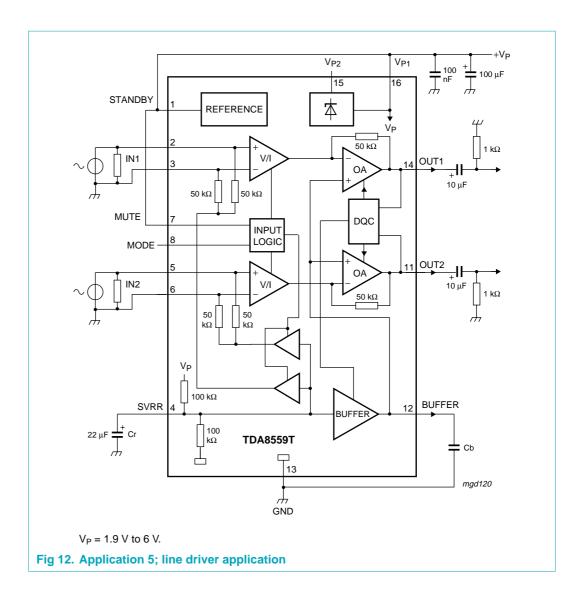


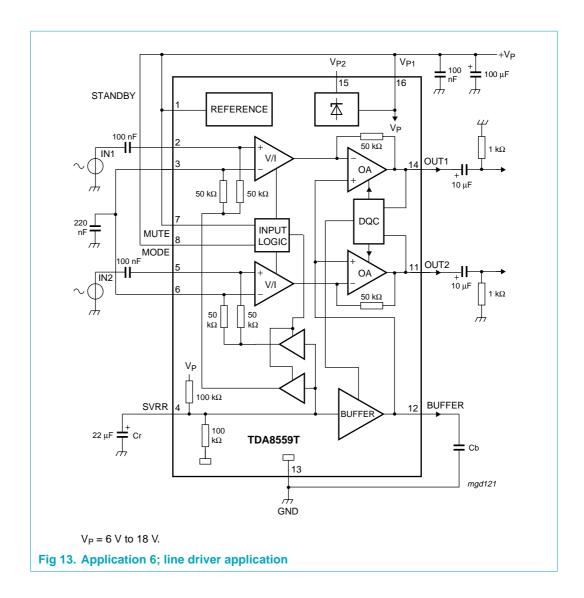
Tig of Application 1, single chaca with loadspeaker capacitor



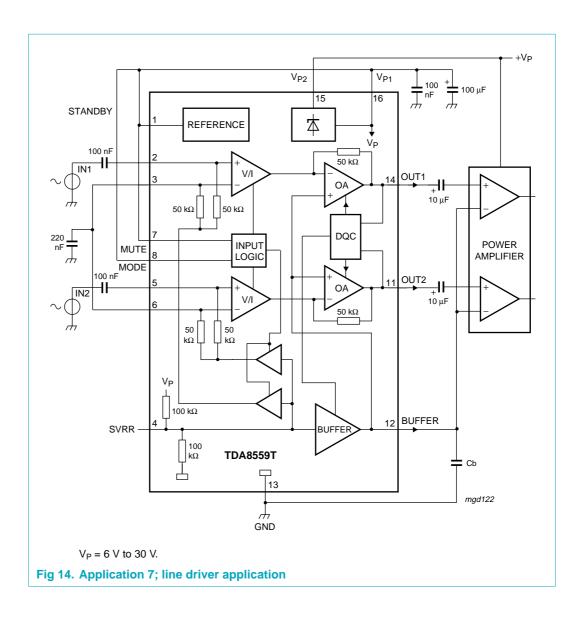








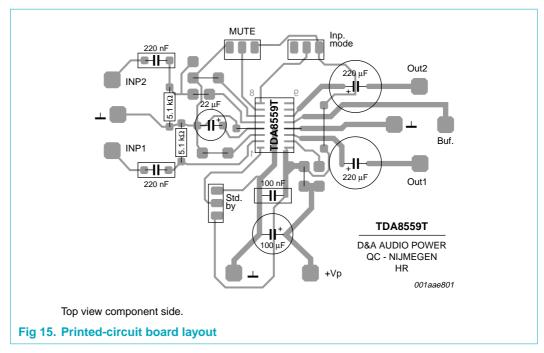
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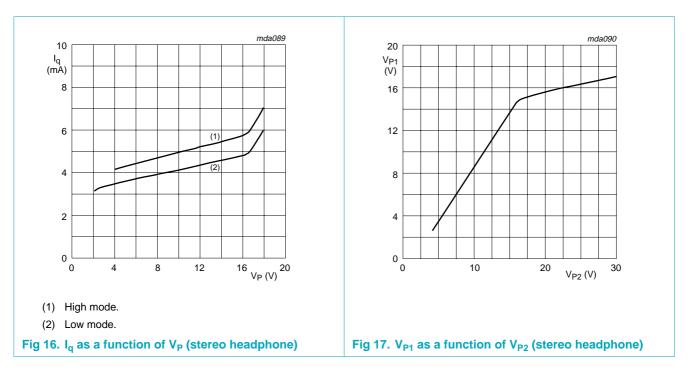
#### Low-voltage stereo headphone amplifier

# 13.14 Printed-circuit board layout

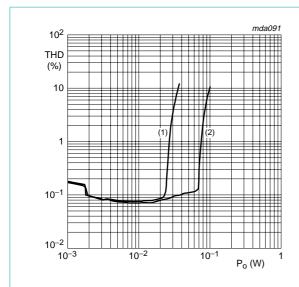


The Printed-Circuit Board (PCB) layout supports all applications as illustrated in <u>Figure 8</u> to <u>Figure 14</u>. The PCB layout has been assembled for input configuration as shown in <u>Figure 3</u>, and output and supply configuration as shown in <u>Figure 8</u> for a maximum supply voltage of 6 V.

### 13.15 Response curves for low input mode



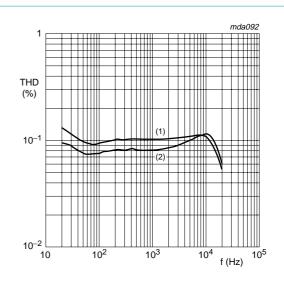
### Low-voltage stereo headphone amplifier



f = 1 kHz.

- (1)  $V_P = 3 V$ ,  $R_L = 32 \Omega$ .
- (2)  $V_P = 5 V$ ,  $R_L = 32 \Omega$ .

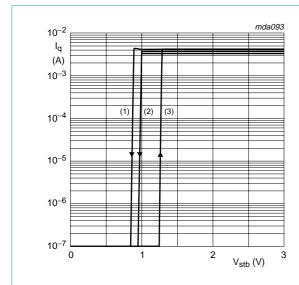
Fig 18. THD as a function of Po (stereo headphone)



 $R_L = 32 \Omega$ .

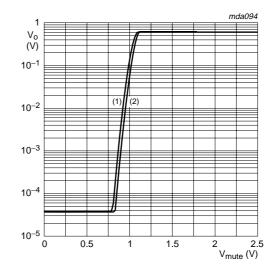
- (1)  $V_P = 5 \text{ V}$ , THD = 50 mW.
- (2)  $V_P = 3 \text{ V}$ , THD = 20 mW.

Fig 19. THD as a function of frequency (stereo headphone)



- (1)  $V_P = 12 \text{ V}.$
- (2)  $V_P = 3 \text{ V} \text{ and } 6 \text{ V}.$
- (3)  $V_P = 3 \text{ V}$ , 6 V and 12 V.

Fig 20.  $I_q$  as a function of  $V_{\text{stb}}$  (stereo headphone)



- (1)  $V_P = 3 V$ .
- (2)  $V_P = 12 \text{ V}.$

Fig 21. V<sub>o</sub> as a function of V<sub>mute</sub> (stereo headphone)

### Low-voltage stereo headphone amplifier

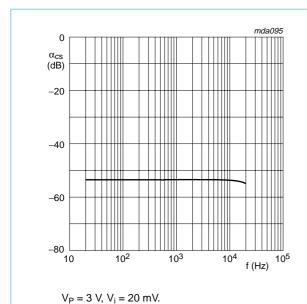
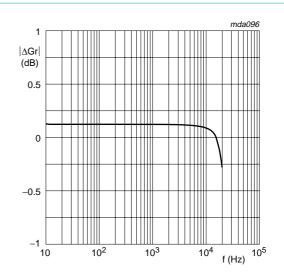


Fig 22. Channel separation as a function of frequency (stereo headphone)



 $V_P = 3 \text{ V}, V_i = 20 \text{ mV}.$ 

Fig 23. Channel unbalance as a function of frequency (stereo headphone)

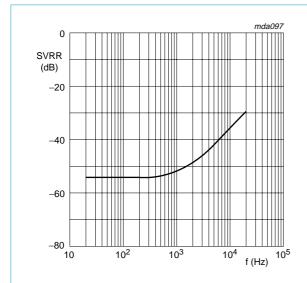
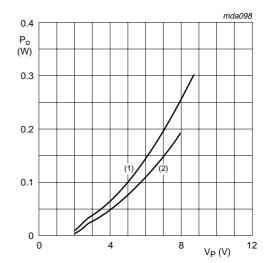


Fig 24. SVRR as a function of frequency (stereo headphone)

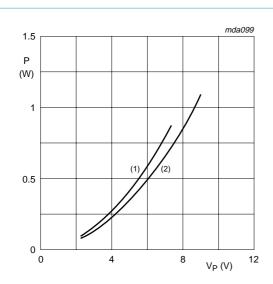
 $V_P = 3 \text{ V}, R_S = 0 \Omega, V_r = 0.2 \text{ V (RMS)}.$ 



- (1)  $R_L = 32 \Omega$ , THD = 10 %.
- (2)  $R_L = 32 \Omega$ , THD = 0.5 %.

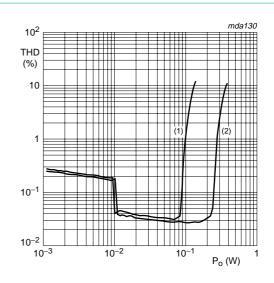
Fig 25.  $P_o$  as a function of  $V_P$  (stereo headphone)

### Low-voltage stereo headphone amplifier



- (1)  $R_L = 25 \Omega$ .
- (2)  $R_L = 32 \Omega$ .

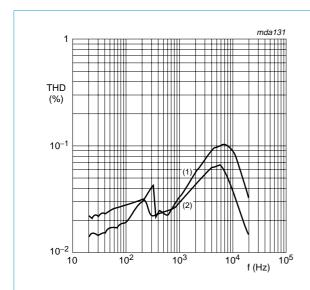
Fig 26. Total worst case power dissipation as a function of supply voltage (SE) (stereo headphone)



f = 1 kHz.

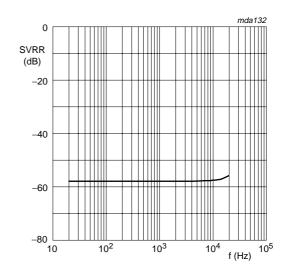
- (1)  $V_P = 3 V$ ,  $R_L = 25 \Omega$ .
- (2)  $V_P = 5 V$ ,  $R_L = 25 \Omega$ .

Fig 27. THD as a function of Po (BTL mono)



- (1)  $V_P = 3 \text{ V}, R_L = 25 \Omega, THD = 70 \text{ mW}.$
- (2)  $V_P = 5~V,~R_L = 25~\Omega,~THD = 150~mW.$

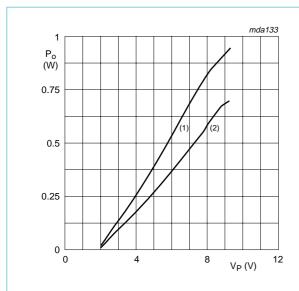
Fig 28. THD as a function of frequency (BTL mono)



 $V_P = 3 \text{ V}, R_s = 0 \Omega, V_r = 0.2 \text{ V (RMS)}.$ 

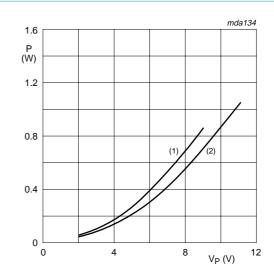
Fig 29. SVRR as a function of frequency (BTL mono)

### Low-voltage stereo headphone amplifier



- (1) THD = 10 %,  $R_L = 25 \Omega$ .
- (2) THD = 0.5 %,  $R_L = 25 \Omega$ .

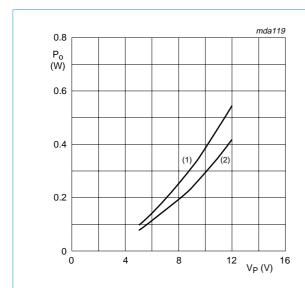
Fig 30. Po as a function of supply voltage (BTL mono)



- (1)  $R_L = 25 \Omega$ .
- (2)  $R_L = 32 \Omega$

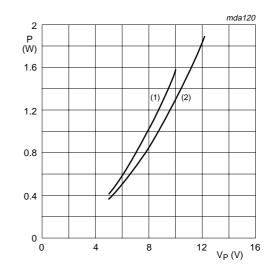
Fig 31. Total worst case power dissipation as a function of supply voltage (BTL mono)

## 13.16 Response curves for high input mode



- (1)  $R_L = 32 \Omega$ , THD = 10 %.
- (2)  $R_L = 32 \Omega$ , THD = 0.5 %.

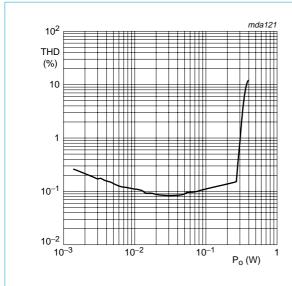
Fig 32.  $P_o$  as a function of  $V_P$  (SE) (BTL mono)



- (1)  $R_L = 25 \Omega$ .
- (2)  $R_L = 32 \Omega$ .

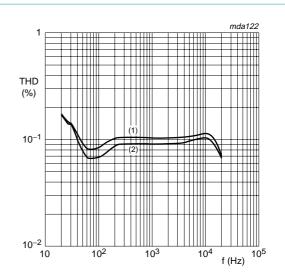
Fig 33. Total worst case power dissipation as a function of supply voltage (SE) (stereo headphone)

### Low-voltage stereo headphone amplifier



 $V_P = 10 \text{ V}, R_L = 32 \Omega, f = 1 \text{ kHz}.$ 

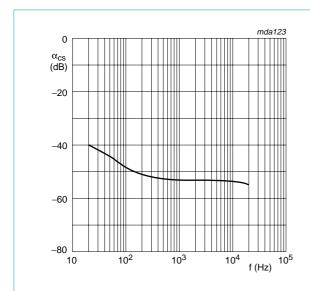
Fig 34. THD as a function of Po (stereo headphone)



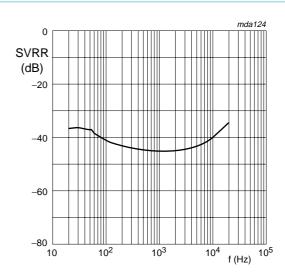
 $V_P = 10 \text{ V}, R_L = 32 \Omega.$ 

- (1)  $P_0 = 100 \text{ mW}.$
- (2)  $P_0 = 50 \text{ mW}.$

Fig 35. THD as a function of frequency (stereo headphone)



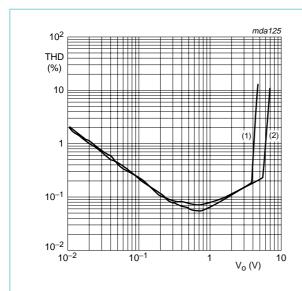
V<sub>P</sub> = 10 V, V<sub>i</sub> = 20 mV. Fig 36. Channel separation as a function of frequency (stereo headphone)



 $V_P = 10 \text{ V}, R_S = 0 \Omega, V_r = 0.2 \text{ V (RMS)}.$ 

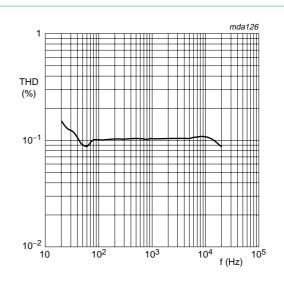
Fig 37. SVRR as a function of frequency (stereo headphone)

### Low-voltage stereo headphone amplifier



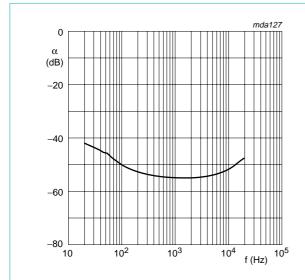
- (1)  $V_P = 12 \text{ V}, R_L = 1 \text{ k}\Omega.$
- (2)  $V_P = 18 \text{ V}, R_L = 1 \text{ k}\Omega.$

Fig 38. THD as a function of Vo (stereo line driver)



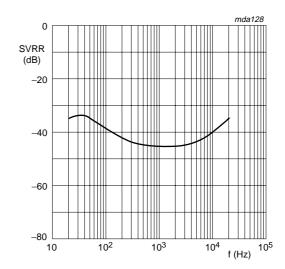
 $V_P = 12 \text{ V}, V_o = 1 \text{ V}.$ 

Fig 39. THD as a function of frequency (stereo line driver)



 $V_P = 12 \text{ V}, V_i = 20 \text{ mV}.$ 

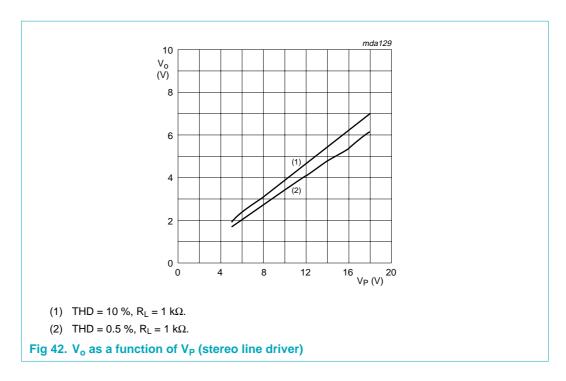
Fig 40. Channel separation as a function of frequency (stereo line driver)



 $V_P$  = 12 V,  $R_S$  = 0  $\Omega$ ,  $V_r$  = 0.2 V (RMS).

Fig 41. SVRR as a function of frequency (stereo line driver)

Low-voltage stereo headphone amplifier



# 14. Test information

# 14.1 Quality information

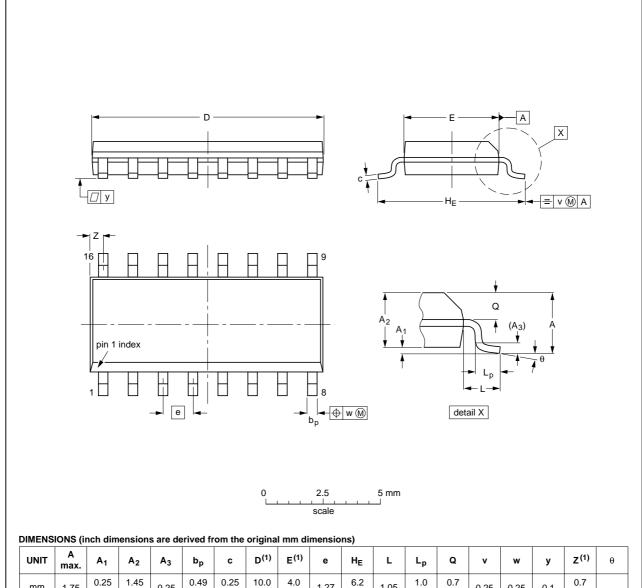
The General Quality Specification for Integrated Circuits, SNW-FQ-611 is applicable.

**TDA8559T** 

# 15. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	ø	v	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DA			
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE		
SOT109-1	076E07	MS-012			<del>99-12-27</del> 03-02-19		

Fig 43. Package outline SOT109-1 (SO16)

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# 16. Soldering

### 16.1 Introduction to soldering surface mount packages

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

#### 16.2 Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Driven by legislation and environmental forces the worldwide use of lead-free solder pastes is increasing.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 seconds and 200 seconds depending on heating method.

Typical reflow temperatures range from 215 °C to 260 °C depending on solder paste material. The peak top-surface temperature of the packages should be kept below:

Table 8. SnPb eutectic process - package peak reflow temperatures (from *J-STD-020C* July 2004)

Package thickness	Volume mm <sup>3</sup> < 350	Volume mm³ ≥ 350
< 2.5 mm	240 °C + 0/–5 °C	225 °C + 0/–5 °C
≥ 2.5 mm	225 °C + 0/–5 °C	225 °C + 0/–5 °C

Table 9. Pb-free process - package peak reflow temperatures (from *J-STD-020C* July 2004)

Package thickness	Volume mm <sup>3</sup> < 350	Volume mm <sup>3</sup> 350 to 2000	Volume mm <sup>3</sup> > 2000
< 1.6 mm	260 °C + 0 °C	260 °C + 0 °C	260 °C + 0 °C
1.6 mm to 2.5 mm	260 °C + 0 °C	250 °C + 0 °C	245 °C + 0 °C
≥ 2.5 mm	250 °C + 0 °C	245 °C + 0 °C	245 °C + 0 °C

Moisture sensitivity precautions, as indicated on packing, must be respected at all times.

## 16.3 Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):

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- larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
- smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time of the leads in the wave ranges from 3 seconds to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### 16.4 Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to  $300\,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 seconds to 5 seconds between 270  $^{\circ}$ C and 320  $^{\circ}$ C.

#### 16.5 Package related soldering information

Table 10. Suitability of surface mount IC packages for wave and reflow soldering methods

•		•
Package[1]	Soldering method	
	Wave	Reflow[2]
BGA, HTSSONT <sup>3</sup> , LBGA, LFBGA, SQFP, SSOPT <sup>3</sup> , TFBGA, VFBGA, XSON	not suitable	suitable
DHVQFN, HBCC, HBGA, HLQFP, HSO, HSOP, HSQFP, HSSON, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable <sup>[4]</sup>	suitable
PLCC[5], SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended[5][6]	suitable
SSOP, TSSOP, VSO, VSSOP	not recommended[7]	suitable
CWQCCNL[8], PMFP[9], WQCCNL[8]	not suitable	not suitable

For more detailed information on the BGA packages refer to the (LF)BGA Application Note (AN01026);
 order a copy from your Philips Semiconductors sales office.

<sup>[2]</sup> All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods.

- [3] These transparent plastic packages are extremely sensitive to reflow soldering conditions and must on no account be processed through more than one soldering cycle or subjected to infrared reflow soldering with peak temperature exceeding 217 °C ± 10 °C measured in the atmosphere of the reflow oven. The package body peak temperature must be kept as low as possible.
- [4] These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- [5] If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- [6] Wave soldering is suitable for LQFP, QFP and TQFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- [7] Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.
- [8] Image sensor packages in principle should not be soldered. They are mounted in sockets or delivered pre-mounted on flex foil. However, the image sensor package can be mounted by the client on a flex foil by using a hot bar soldering process. The appropriate soldering profile can be provided on request.
- [9] Hot bar soldering or manual soldering is suitable for PMFP packages.

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# 17. Revision history

## Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TDA8559_3	20060515	Product data sheet	-	TDA8559_2
Modifications:	information s	f this data sheet has been rede standard of Philips Semicondud 39-1) package removed	•	th the new presentation and
TDA8559_2 (9397 750 02066)	19970627	Product specification	-	TDA8559_1
TDA8559_1 (9397 750 00546)	19960102	Preliminary specification	-	-

#### Low-voltage stereo headphone amplifier

# 18. Legal information

#### 18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.semiconductors.philips.com">http://www.semiconductors.philips.com</a>.

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For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

### Low-voltage stereo headphone amplifier

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